GSM4637W

40V P-Channel Enhancement Mode MOSFET

Product Description

GSM4637W, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

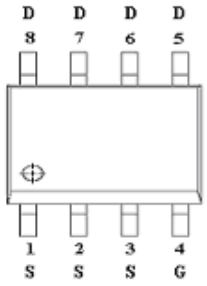
- -40V/-6.8A,$R_{DS(ON)}$=37mΩ@V_{GS}=-10V
- -40V/-5.8A,$R_{DS(ON)}$=54mΩ@V_{GS}=-4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- SOP-8P package design

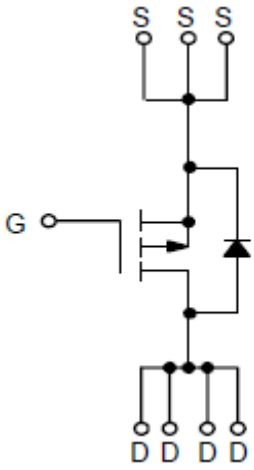
Applications

- Backlight Inverter for LCD Display
- Full Bridge DC/DC Converter
- Load Switch
- CCFL Inverter

Packages & Pin Assignments

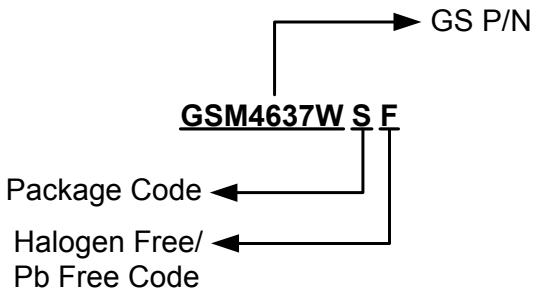
GSM4637WSF(SOP-8P)





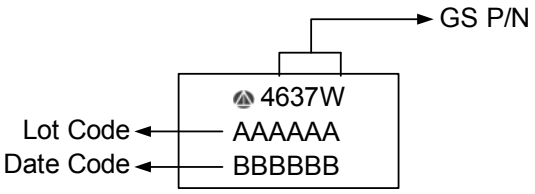
Pin	Description	Pin	Description
1	Source	5	Drain
2	Source	6	Drain
3	Source	7	Drain
4	Gate	8	Drain

Ordering Information



Part Number	Package	Quantity Reel
GSM4637WSF	SOP-8P	2500 PCS

Marking Information



Absolute Maximum Ratings

T_A=25ºC unless otherwise noted

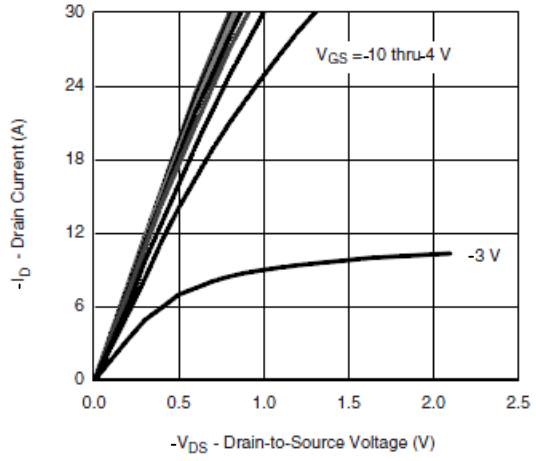
Symbol	Parameter		Typical	Unit
V_{DSS}	Drain-Source Voltage		-40	V
V_{GSS}	Gate –Source Voltage		±20	V
I_D	Continuous Drain Current(T_J=150℃)	T_A=25ºC	-6.8	A
		T_A=70ºC	-5.8	
I_{DM}	Pulsed Drain Current		-20	
I_S	Continuous Source-Drain Diode Current		-2	
P_D	Power Dissipation	T_A=25ºC	2.8	W
		T_A=70ºC	1.8	
T_J	Operating Junction Temperature		150	ºC
T_{STG}	Storage Temperature Range		-55/150	ºC
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		62.5	ºC/ W

Electrical Characteristics

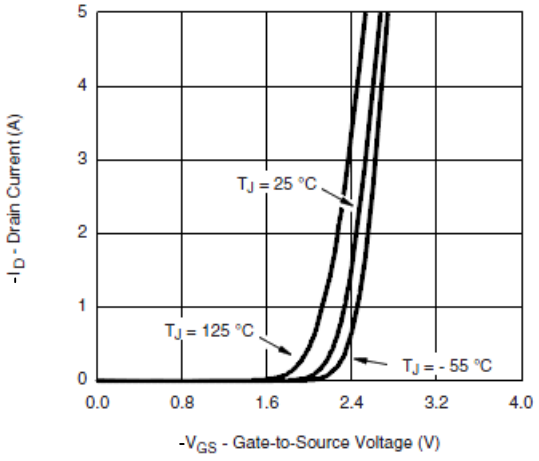
T_A=25ºC unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=-250uA	-40			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=-250uA	-1.5		-3.0	
I_{GSS}	Gate Leakage Current	V_{DS}=0V,V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-40V,V_{GS}=0V			-1	uA
		V_{DS}=-40V, V_{GS}=0V,T_J=85ºC			-20	
$I_{D(on)}$	On-State Drain Current	V_{DS}≦-5V,V_{GS}=-10V	-20			A
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=-10V,I_D=-6.8A		30	37	mΩ
		V_{GS}=-4.5V,I_D=-5.8A		44	54	
g_{fs}	Forward Transconductance	V_{DS}=-15V,I_D=-5A		20		S
V_{SD}	Diode Forward Voltage	I_S=-2A,V_{GS}=0V		-0.8	-1.2	V
Dynamic						
C_{iss}	Input Capacitance	V_{DS}=-20V, V_{GS}=0V,f=1MHz		1100		pF
C_{oss}	Output Capacitance			145		
C_{rss}	Reverse Transfer Capacitance			115		
Q_g	Total Gate Charge	V_{DS}=-20V, V_{GS}=-4.5V,I_D=-5.0A		13	20	nC
Q_{gs}	Gate-Source Charge			4.5		
Q_{gd}	Gate-Drain Charge			6.5		
$t_{d(on)}$	Turn-On Time	V_{DD}=-20V, R_L=4Ω,I_D=-5.0A, V_{GEN}=-4.5V,R_G=1Ω		40	80	ns
t_r				55	100	
$t_{d(off)}$	Turn-Off Time			30	60	
t_F				12	20	

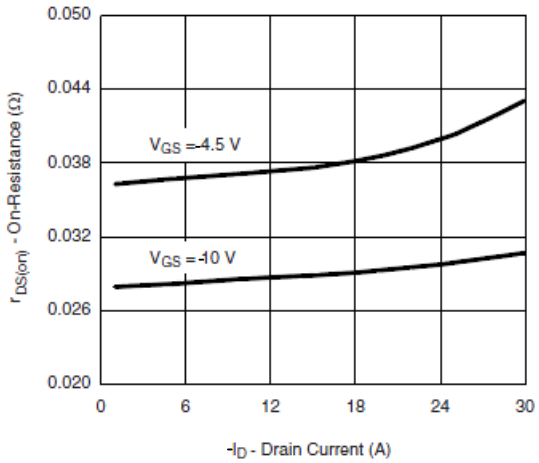
Typical Performance Characteristics



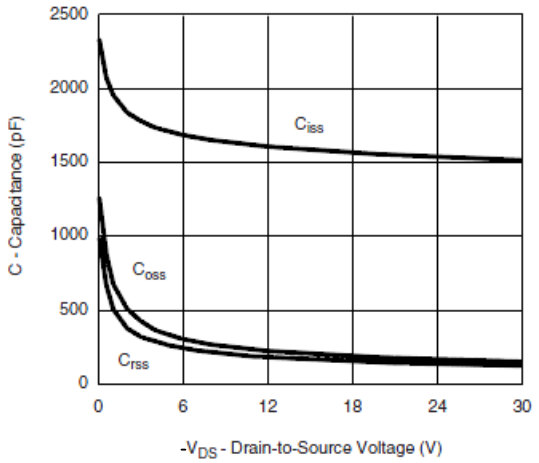
Output Characteristics



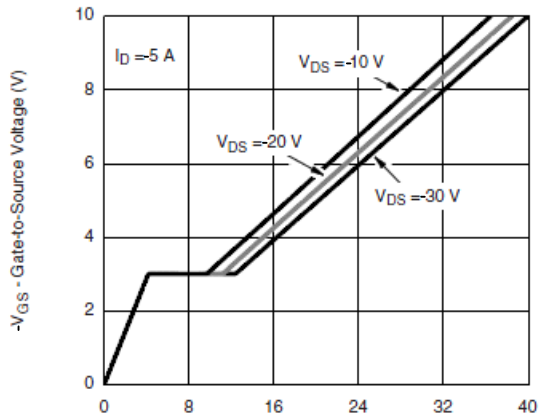
Transfer Characteristics



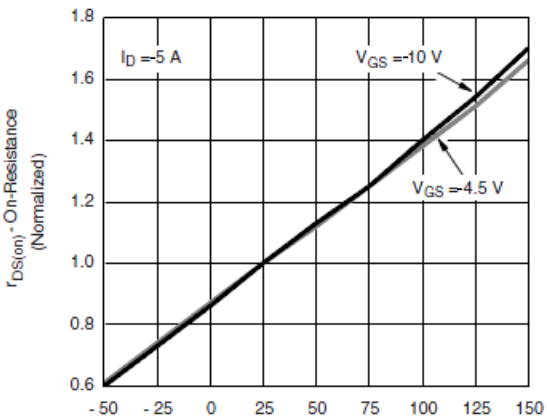
On-Resistance vs. Drain Current



Capacitance

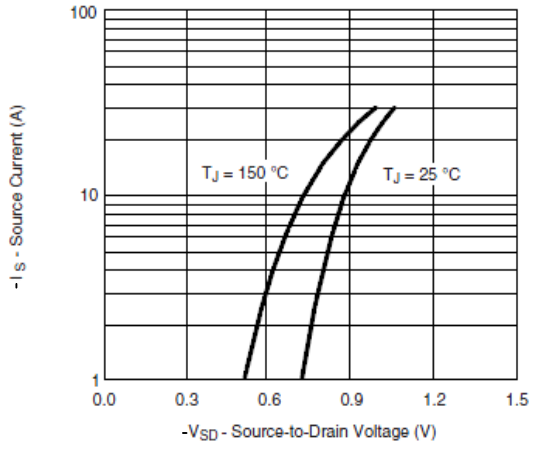


Gate Charge

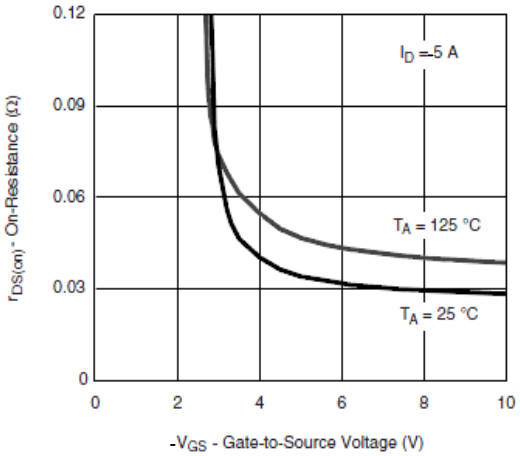


On-Resistance vs. Junction Temperature

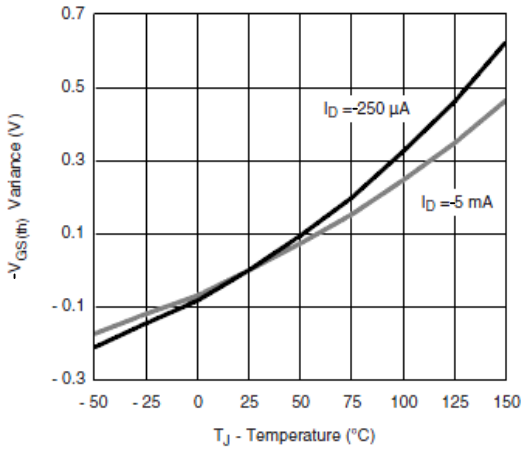
Typical Performance Characteristics (continue)



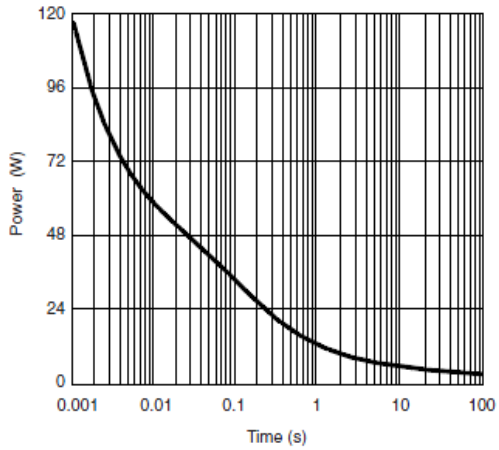
Source-Drain Diode Forward Voltage



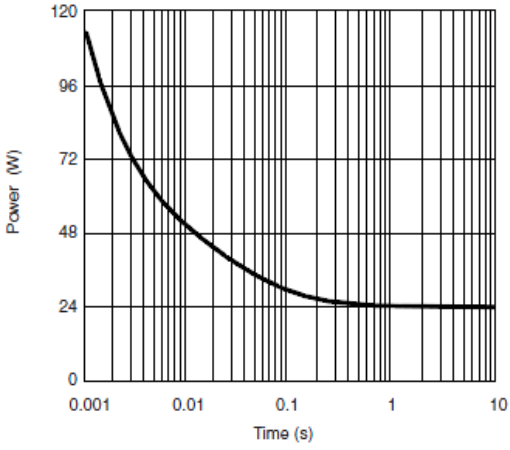
On-Resistance vs. Gate-to-Source Voltage



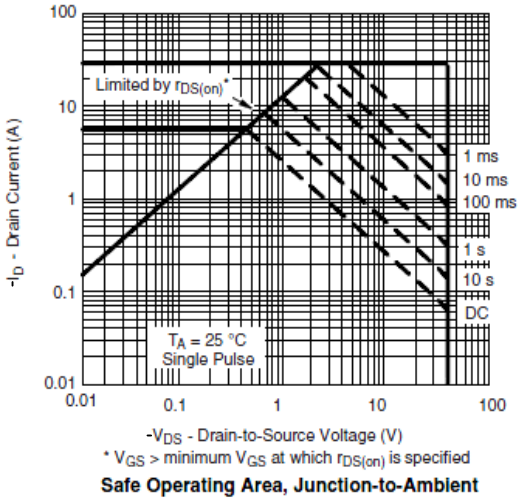
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



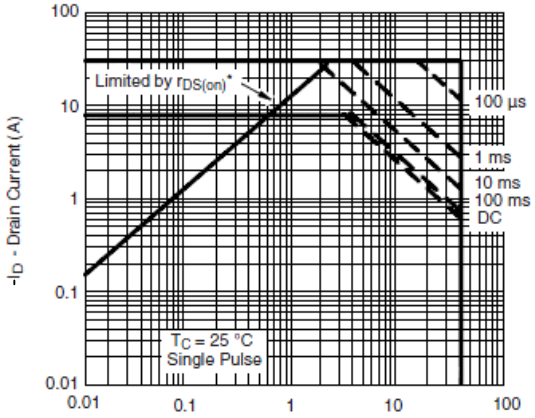
Single Pulse Power, Junction-to-Case



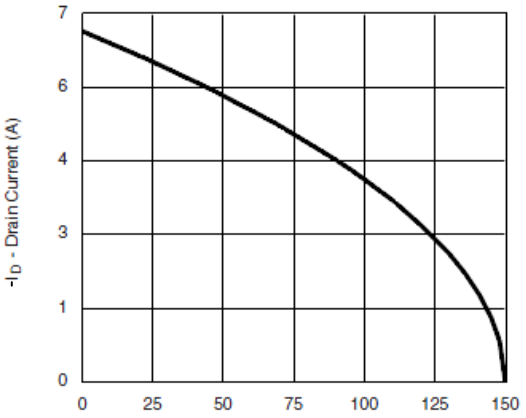
* V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

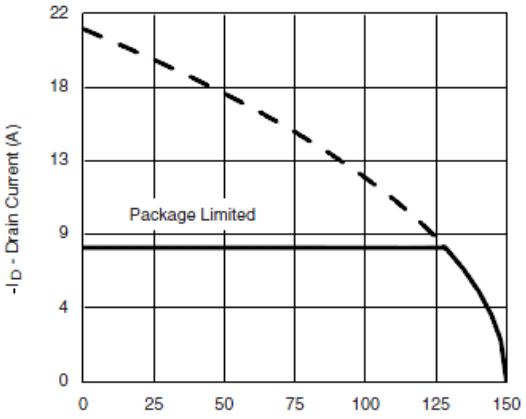
Typical Performance Characteristics (continue)



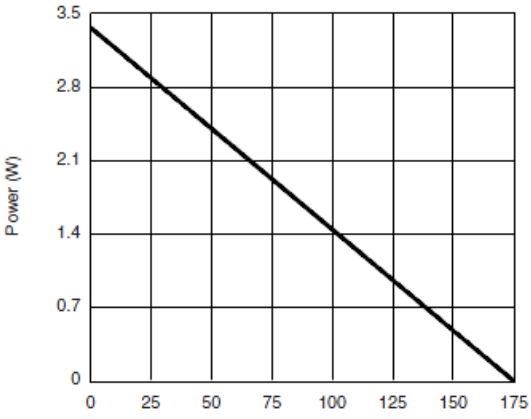
Safe Operating Area, Junction-to-Case



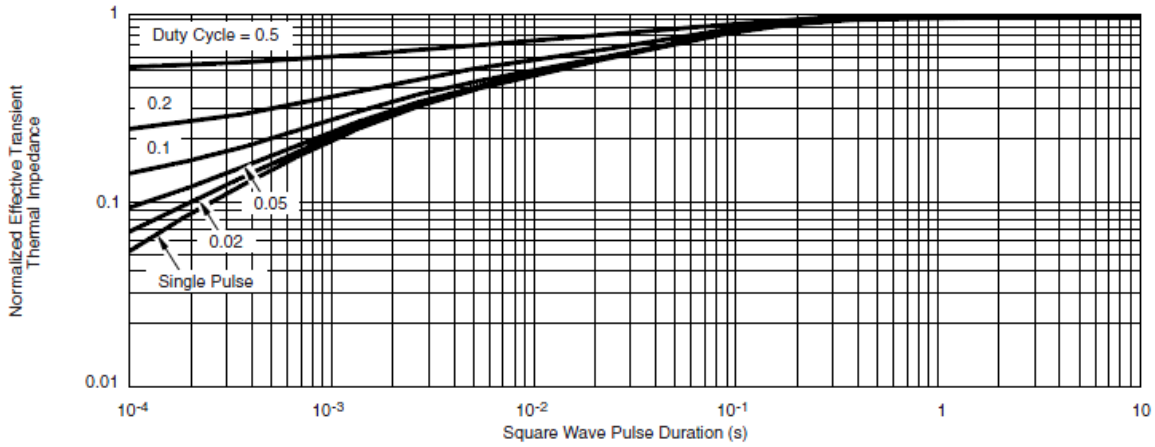
Current Derating*, Junction-to-Ambient



Current Derating*, Junction-to-Case



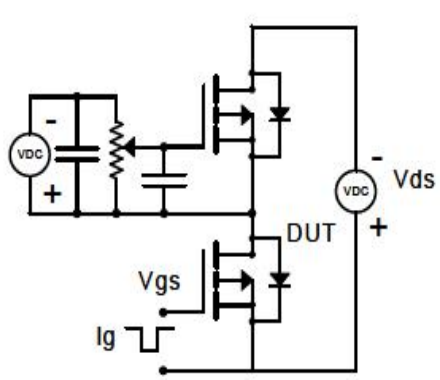
Power Derating*, Junction-to-Ambient

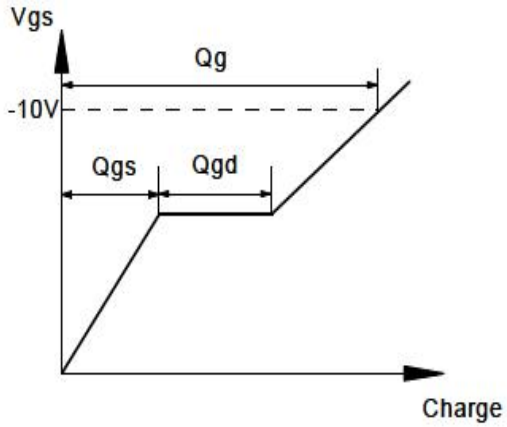


Normalized Thermal Transient Impedance, Junction-to-Case

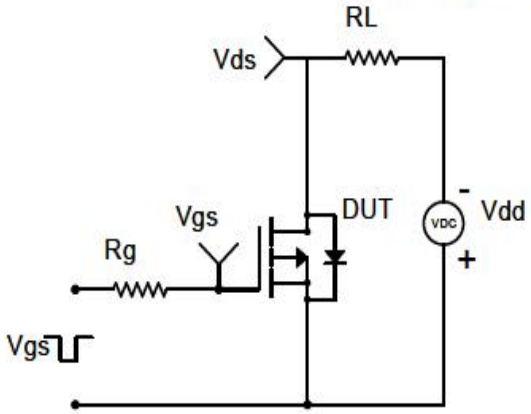
Typical Performance Characteristics (continue)

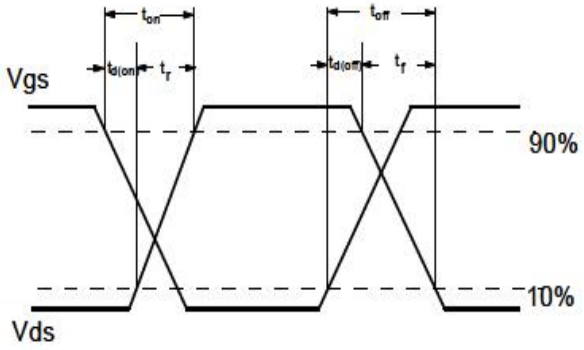
Gate Charge Test Circuit & Waveform



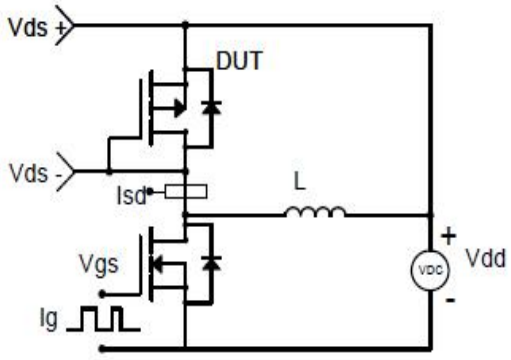


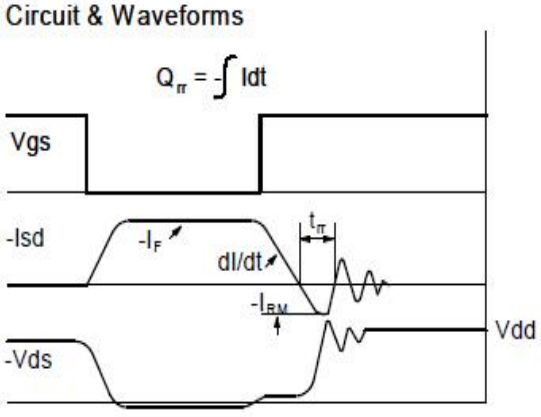
Resistive Switching Test Circuit & Waveforms





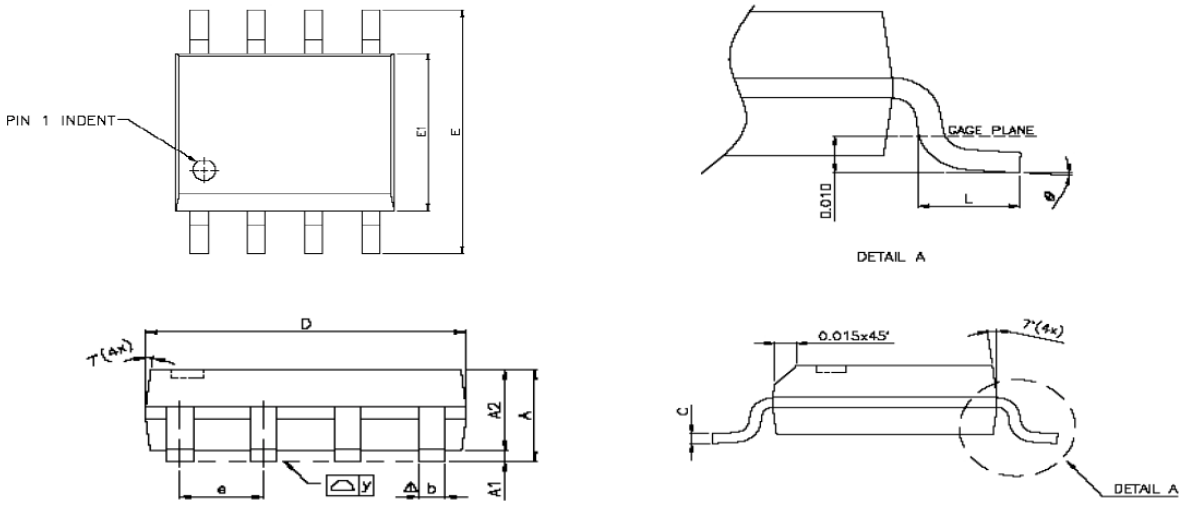
Diode Recovery Test Circuit & Waveforms





Package Dimension

SOP-8P PLASTIC PACKAGE



Dimensions						
Symbol	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	-	0.25	0.004	-	0.010
A2	-	1.45	-	-	0.057	-
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	-	1.27	-	-	0.050	-
L	0.38	0.71	1.27	0.015	0.028	0.050
2 y	-	-	0.076	-	-	0.003
θ	0°	-	8°	0°	-	8°

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